

PRN No.	
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PAPER CODE	V213-292 (RE)
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December 2023 (REEXAM)

SY B.TECH (SEMESTER - I)

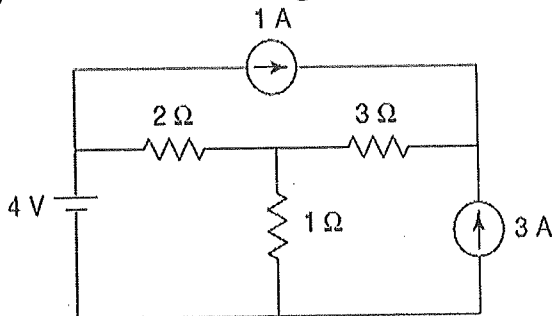
COURSE NAME: Engineering Circuit Analysis Branch: E&TC COURSE CODE: ETUA21202
(PATTERN 2020)

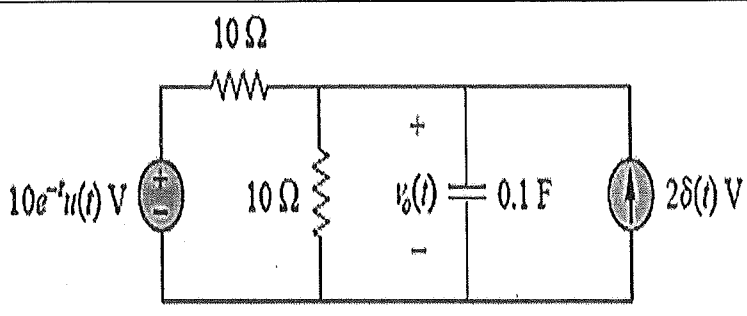
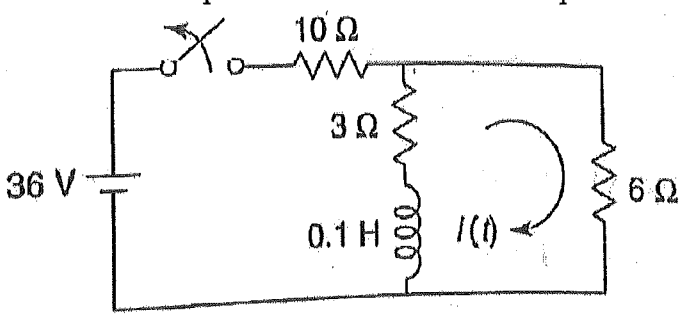
Time: [2 Hrs]

[Max. Marks: 60]

(*) Instructions to candidates:

- 1) Figures to the right indicate full marks.
- 2) Use of scientific calculator is allowed
- 3) Use suitable data wherever required
- 4) All questions are compulsory. Solve any two sub questions each from each Question 1, 2, 3, 4, 5, and 6 respectively

Q. No.	Question Description	Max. Marks	CO mapped	BT Level
Q.1	a) Draw and Explain equivalent diagram of Thevenin's and Norton's circuit	[5]	CO1	Understand
	b) Find current through 1 ohm	[5]	CO1	Analysis
		[5]	CO1	Analysis
Q2	c) Derive the expression for maximum power transfer condition applied to reactive network	[5]	CO1	Analysis
	a) Draw and Explain the voltage phasor diagrams for series R-L-C circuit	[5]	CO2	Understand
	b) Justify the parallel resonance circuit as a current amplifier	[5]	CO2	Analysis
Q3.	c) Design LPF T-section with $F_c=2500$ Hz and $R_o=1\text{Kohm}$. Also compute attenuation in neper at 3000Hz and 2000Hz.	[5]	CO2	Analysis
	a) Draw and Explain initial conditions for inductor and capacitor with the help of circuit diagram	[5]	CO3	Understand
	b) Determine $V_o(t)$ using Laplace Transform. Assume $V_o(0)=5\text{V}$.	[5]	CO3	Analysis

	 <p>c) The switch is opened at $t=0$. Find the expression for $i(t)$</p> 			
Q.4	<p>a) Sketch the construction of N channel JFET and explain its working.</p> <p>b) Analyze Common Source with bypass capacitor amplifier circuit using N channel JFET to determine parameters as voltage gain (A_v), input impedance (Z_i) and output impedance (Z_o).</p> <p>c) Self-bias circuit using N channel JFET has following parameters: $I_{DSS}=6\text{mA}$, $V_P=4\text{V}$, $V_{DD}=20\text{V}$, $R_D=3.3\text{K}\Omega$, $R_S=1\text{K}\Omega$ and $R_G=1\text{M}\Omega$. Find the values of operating point parameters as I_{DQ}, V_{DSQ} and V_{GSQ}</p>	[5]	CO4	Understand
Q.5	<p>a) Explain following terms related to MOSFET:</p> <p>i) Sub-threshold conduction</p> <p>ii) Body effect</p> <p>b) Elaborate any three non-ideal effects in MOSFET.</p> <p>c) For Common source amplifier with voltage divider biasing circuit using N channel E-MOSFET, following parameters are given $V_{DD}=5\text{V}$, $R_1=520\text{k}\Omega$, $R_2=320\text{k}\Omega$, $R_D=10\text{k}\Omega$, and $R_S=0$. Assume transistor parameters as $V_{tn}=0.8\text{V}$, $K_n=0.40\text{mA/V}^2$, and $\lambda=0$. Determine g_m, r_o, small signal voltage gain (A_v) and output resistances R_o</p>	[5]	CO5	Understand
		[5]	CO5	Understand
		[5]	CO5	Apply

Q.6)	a) Sketch block diagrams of voltage series and voltage shunt negative feedback topologies.	[5]	CO6	Understand
	b) Sketch RC phase shift oscillator and calculate oscillating frequency if $R = 6.5 \text{ K}\Omega$ and $C = 0.01 \text{ }\mu\text{F}$.	[5]	CO6	Apply
	c) Calculate the voltage gain (A_f), input impedance (Z_{if}) and output impedance (Z_{of}) for voltage-series feedback amplifier having $A = -100$, $R_i = 10 \text{ k}\Omega$, and $R_o = 20 \text{ k}\Omega$, feedback factor (β) = - 0.1.	[5]	CO6	Apply

